

1 1. A method comprising:
2 modifying the viscosity of a wet etchant; and
3 applying said etchant to a semiconductor layer.

1 2. The method of claim 1 including increasing the
2 viscosity of the etchant.

1 3. The method of claim 2 where increasing the
2 viscosity of a wet etchant includes adding a thickening
3 agent to said wet etchant.

1 4. The method of claim 2 where increasing the
2 viscosity of a wet etchant includes dehydrating said wet
3 etchant.

1 5. The method of claim 2 including forming a mask
2 over a layer to be etched and applying said wet etchant
3 through said mask to the layer to be etched.

1 6. The method of claim 5 including dipping a
2 semiconductor wafer in a bath of said etchant of increased
3 viscosity.

1 7. The method of claim 2 including forming a stack
2 on a semiconductor wafer including a metal layer to be
3 etched, forming a mask over said metal layer, and etching
4 said metal layer with said increased viscosity etchant.

1 8. A method comprising:
2 increasing the viscosity of a wet etchant to
3 reduce the amount of undercutting of an etched layer.

1 9. The method of claim 8 including increasing the
2 viscosity of a wet etchant by dehydrating the etchant.

1 10. The method of claim 8 including increasing the
2 viscosity of the etchant by adding a thickening agent to
3 said etchant.

1 11. The method of claim 8 including applying said
2 increased viscosity wet etchant to a semiconductor wafer to
3 etch a layer on said wafer.

1 12. A wet etchant comprising:
2 a material to etch a semiconductor layer; and
3 a thickening agent.

1 13. The etchant of claim 12 wherein said thickening
2 agent is glycol.

1 14. The etchant of claim 12 wherein said thickening
2 agent is glycerol.

1 15. The etchant of claim 12 wherein said etchant is
2 sulfuric acid.

1 16. A wet etchant comprising:
2 a dehydrated etching material.

1 17. The etchant of claim 16 wherein said material is
2 sulfuric acid.

1 18. A wet etchant comprising:
2 a material to etch a semiconductor layer, said
3 material having a viscosity of greater than one centipoise.

1 19. The etchant of claim 18 wherein said etchant is
2 dehydrated.

1 20. The etchant of claim 18 including a thickening
2 agent.

1 21. The etchant of claim 18 including sulfuric acid.